

PJW3N10A

100V N-Channel Enhancement Mode MOSFET

Voltage 100 V Current 2.2 A

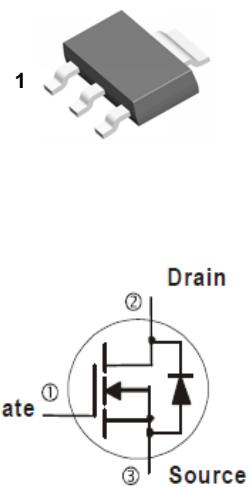
Features

- $R_{DS(ON)}$, $V_{GS} @ 10V, I_D @ 2.2A < 310m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ 4.5V, I_D @ 1A < 320m\Omega$
- Low On-Resistance
- Low input capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123 grams
- Marking: W3N10A

SOT-223



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	+20	V
Continuous Drain Current	$T_A=25^\circ C$	I_D	2.2	A
	$T_A=70^\circ C$		1.7	
Pulsed Drain Current ^(Note 1)		I_{DM}	4.4	A
Power Dissipation	$T_A=25^\circ C$	P_D	3.1	W
	$T_A=70^\circ C$		2.0	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Typical Thermal resistance - Junction to Ambient, $t \leq 10s$ ^(Note 5)		$R_{\theta JA}$	40.3	°C/W

- Limited only By Maximum Junction Temperature

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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	100	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1.0	2.06	2.5	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=2.2\text{A}$	-	284	310	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=1.0\text{A}$	-	287	320	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=80\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1.0	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	$V_{\text{DS}}=50\text{V}, I_{\text{D}}=2.2\text{A}, V_{\text{GS}}=10\text{V}$ (Note 1,2)	-	9.1	-	nC
Gate-Source Charge	Q_{gs}		-	2.1	-	
Gate-Drain Charge	Q_{gd}		-	1.4	-	
Input Capacitance	C_{iss}	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}, f=1.0\text{MHZ}$	-	508	-	pF
Output Capacitance	C_{oss}		-	29	-	
Reverse Transfer Capacitance	C_{rss}		-	18	-	
Turn-On Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=50\text{V}, I_{\text{D}}=2.2\text{A}, V_{\text{GS}}=10\text{V}, R_{\text{G}}=6\Omega$ (Note 1,2)	-	2	-	ns
Turn-On Rise Time	t_{r}		-	21	-	
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	12	-	
Turn-Off Fall Time	t_{f}		-	19	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_{S}	---	-	-	2.2	A
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=1\text{A}, V_{\text{GS}}=0\text{V}$	-	0.78	1.2	V

NOTES :

1. Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4. Repetitive rating, pulse width limited by junction temperature $T_J(\text{MAX})=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25^\circ\text{C}$.
5. R_{eJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

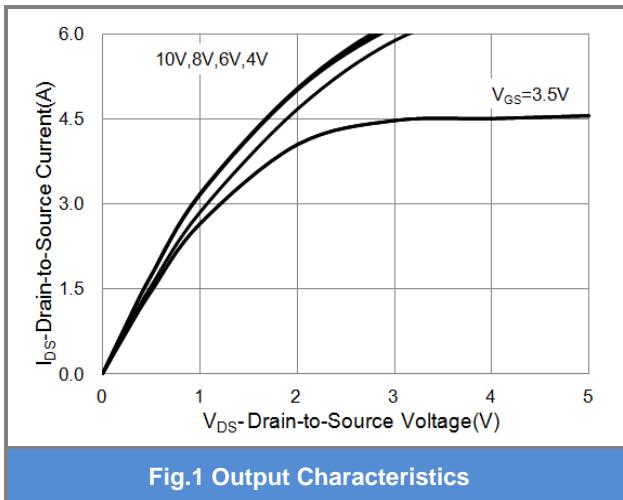


Fig.1 Output Characteristics

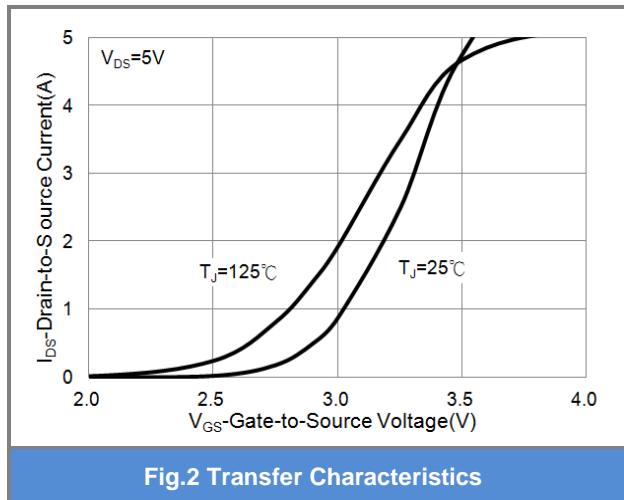


Fig.2 Transfer Characteristics

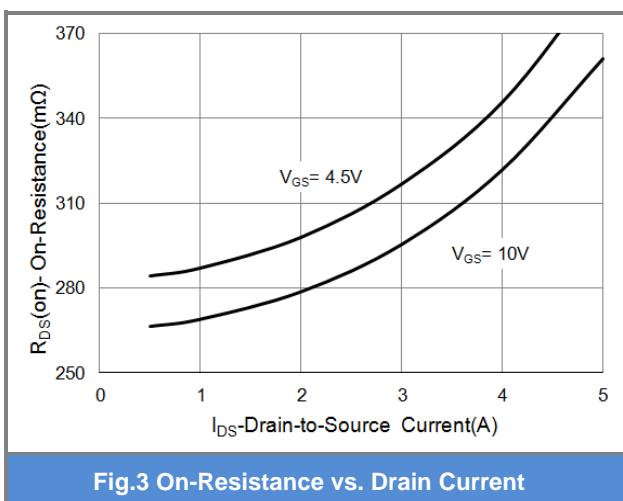


Fig.3 On-Resistance vs. Drain Current

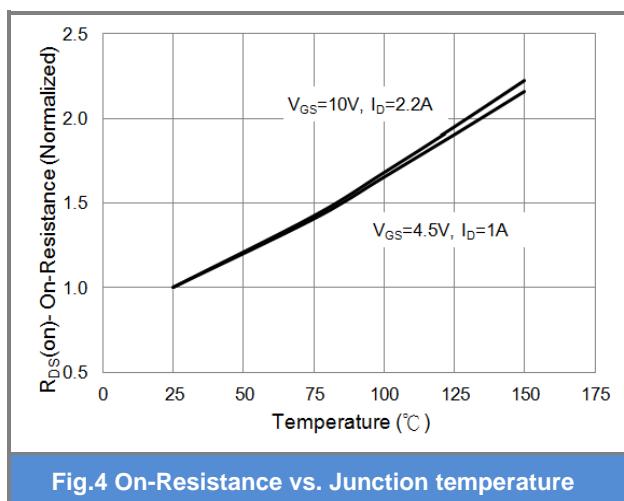


Fig.4 On-Resistance vs. Junction temperature

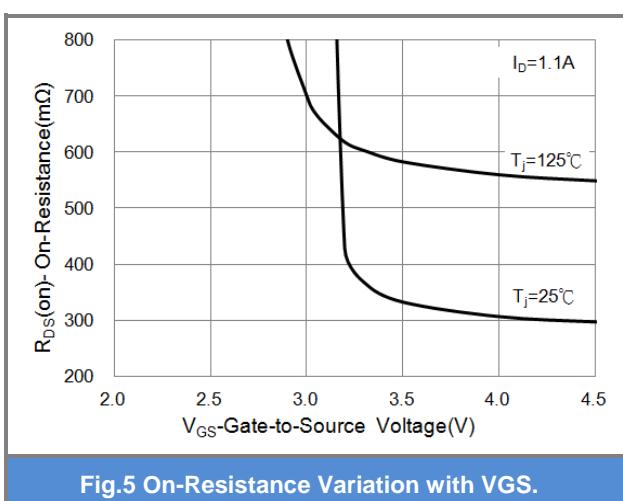


Fig.5 On-Resistance Variation with VGS.

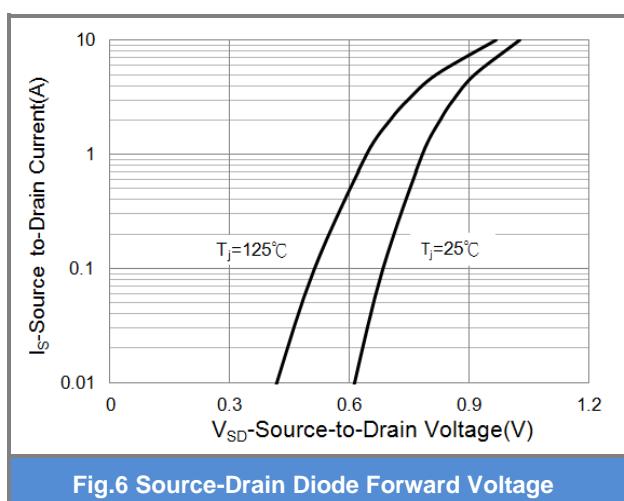


Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

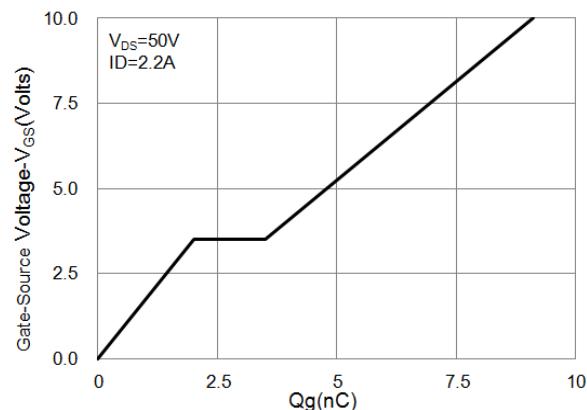


Fig.7 Gate-Charge Characteristics

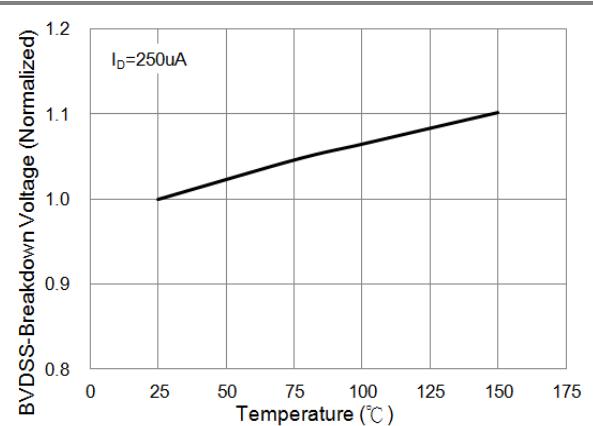


Fig.8 Breakdown Voltage Variation vs. Temperature

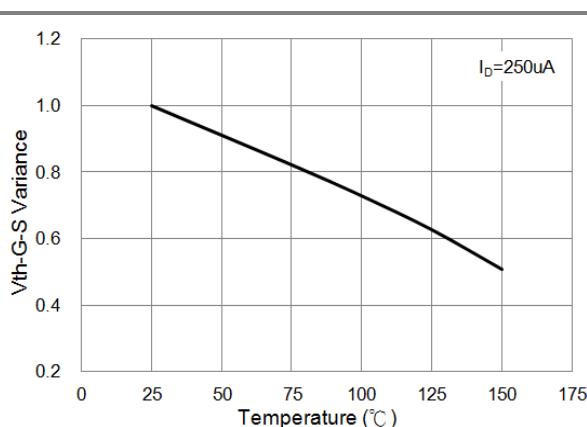


Fig.9 Threshold Voltage Variation with Temperature

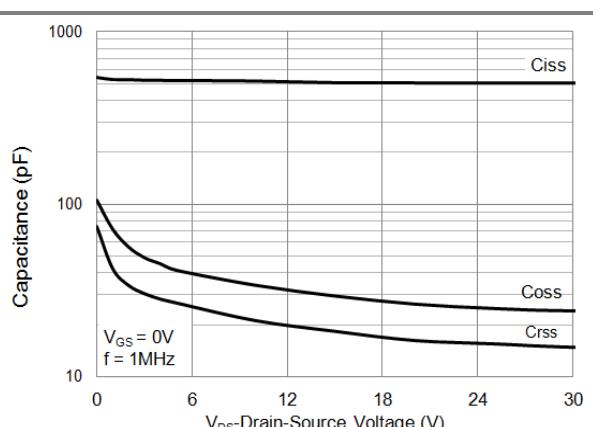


Fig.10 Capacitance vs. Drain-Source Voltage

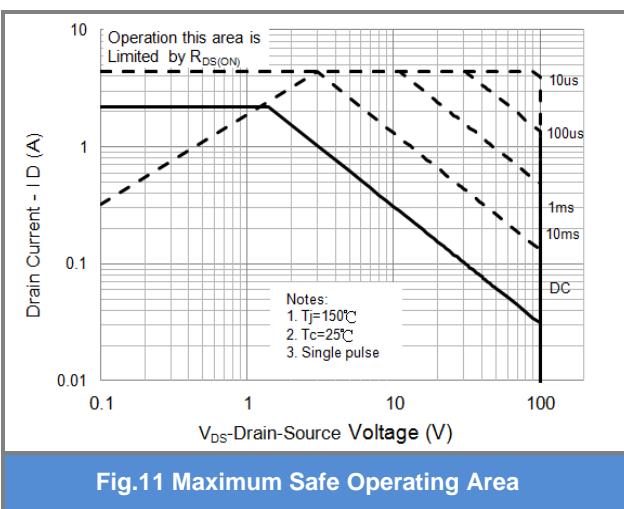
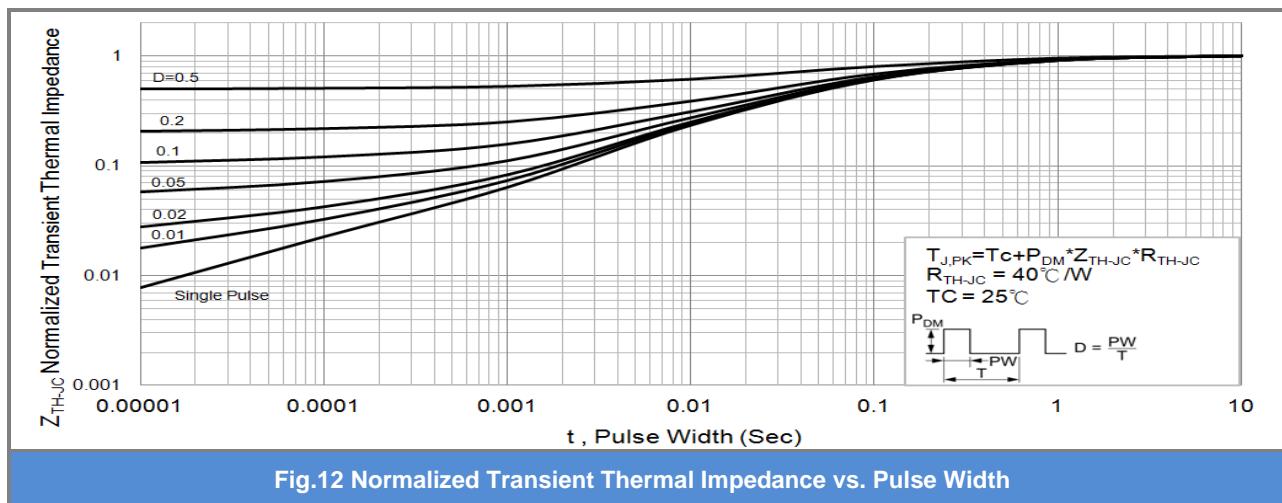


Fig.11 Maximum Safe Operating Area

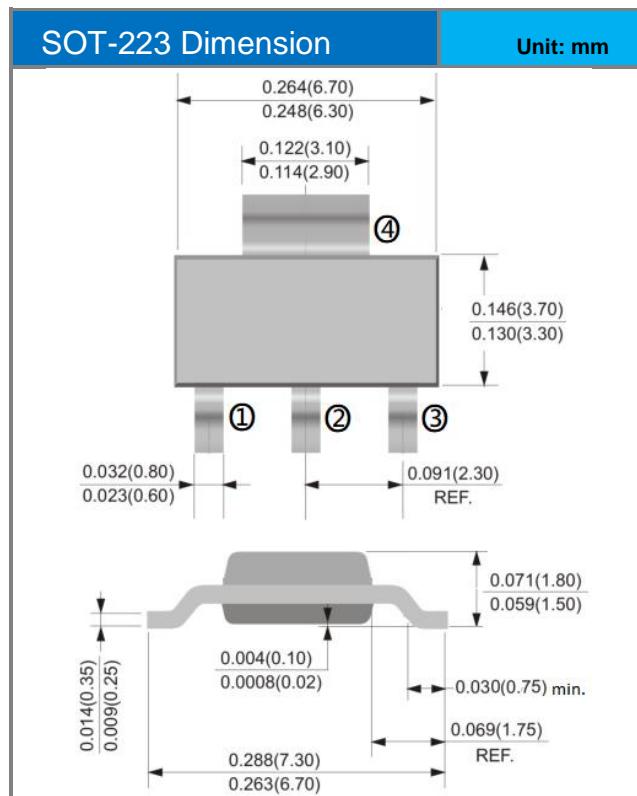
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TYPICAL CHARACTERISTIC CURVES



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Packaging Information

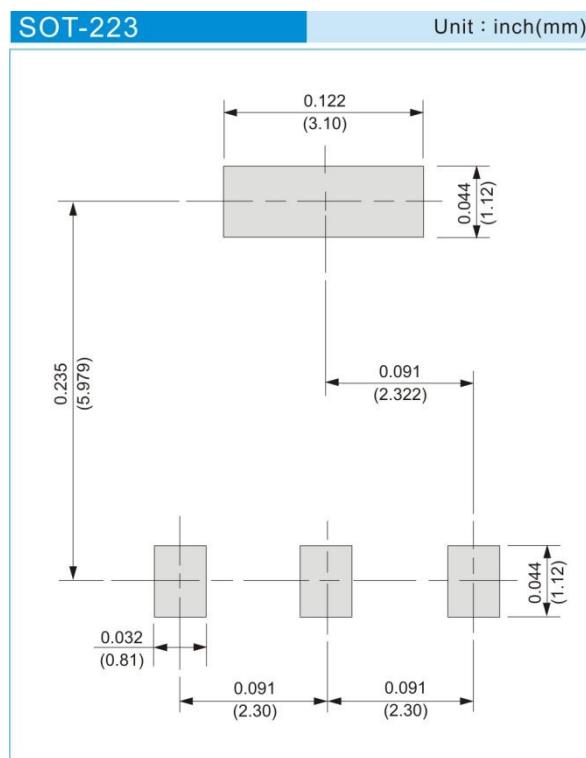


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Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJW3N10A	SOT-223	2.5K pcs / 13" reel	W3N10A

Mounting Pad Layout



PJW3N10A

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